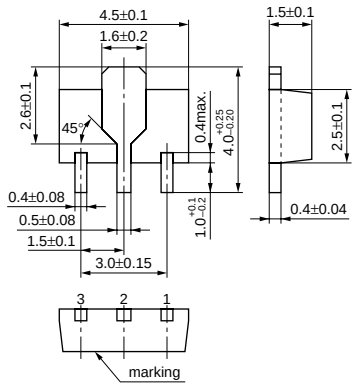
2SC5019

Silicon NPN epitaxial planer type

For UHF band low-noise amplification

Unit: mm



1:Base
2:Collector EIAJ:SC–62
3:Emitter Mini Power Type Package

Marking symbol : W

Features

- Low noise figure NF.
- High gain.
- High transition frequency f_T.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25˚C)

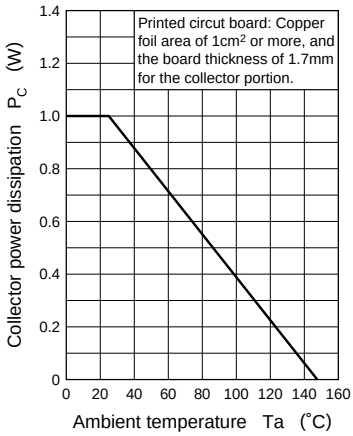
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	10	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	80	mA
Collector power dissipation	P_C*	1	W
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion

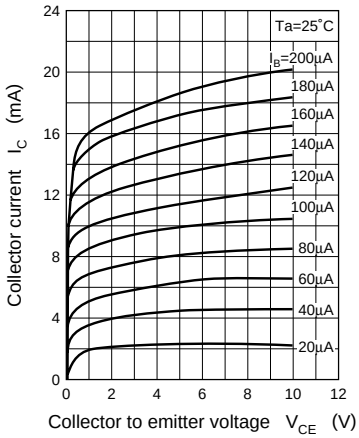
Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 10V, I_E = 0			1	µA
Emitter cutoff current	I_{EBO}	V_{EB} = 2V, I_C = 0			1	µA
Collector to base voltage	V_{CBO}	I_C = 10µA, I_E = 0	15			V
Collector to emitter voltage	V_{CEO}	I_C = 100µA, I_B = 0	10			V
Forward current transfer ratio	h_{FE}	V_{CE} = 8V, I_C = 20mA	80		250	
Transition frequency	f_T	V_{CE} = 8V, I_C = 20mA, f = 800MHz	5	6		GHz
Collector output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz		0.9	1.2	pF
Foward transfer gain	$\|S_{21e}\|^2$	V_{CE} = 8V, I_C = 20mA, f = 800MHz	7.5	10		dB
Maximum unilateral power gain	GUM	V_{CE} = 8V, I_C = 20mA, f = 800MHz		11.5		dB
Noise figure	NF	V_{CE} = 8V, I_C = 20mA, f = 800MHz		1.7		dB

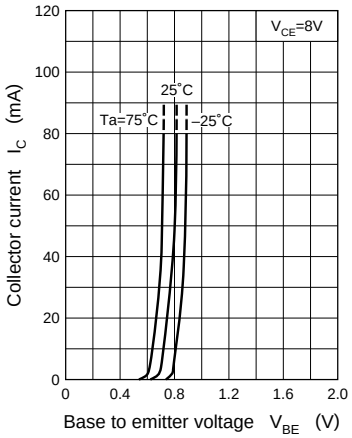
P_C — Ta



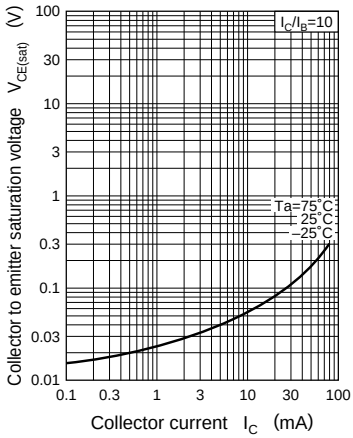
I_C — V_{CE}



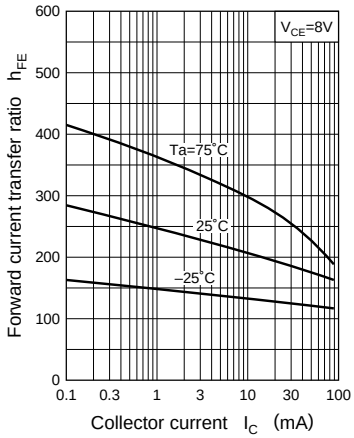
I_C — V_{BE}



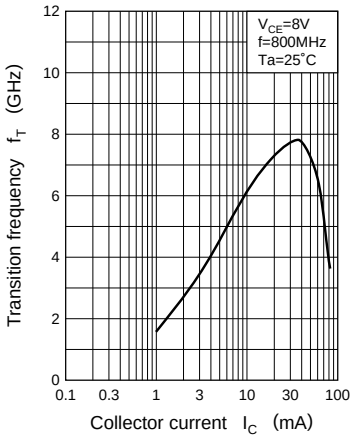
$V_{CE(sat)}$ — I_C



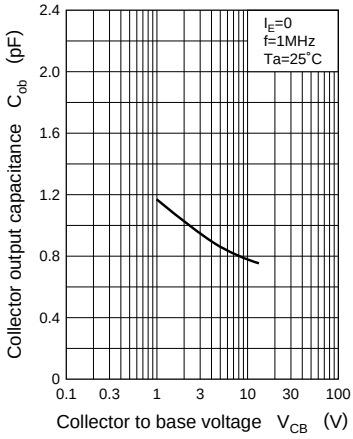
h_{FE} — I_C



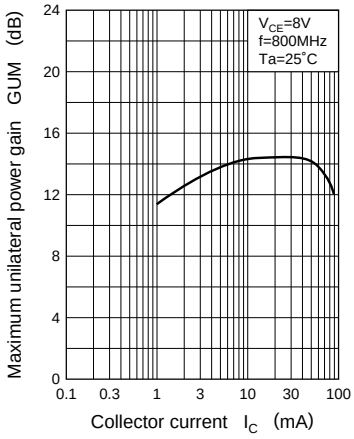
f_T — I_C



C_{ob} — V_{CB}



GUM — I_C



NF — I_C

